

Isc N-Channel MOSFET Transistor

STB22NM60N

• FEATURES

- · Low input capacitance and gate charge
- Low gate input resistances
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

Switching applications

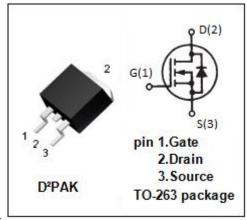


• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	600	V
V _{GSS}	Gate-Source Voltage	±30	V
I _D	Drain Current-Continuous@ T_C =25° C T_C =100° C	16 10	А
I _{DM}	Drain Current-Single Pulsed	64	А
P_D	Total Dissipation	125	W
Tj	Operating Junction Temperature	-55~150	$^{\circ}$ C
T _{stg}	Storage Temperature	-55~150	$^{\circ}$ C

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	1.0	°C/W



B	K		L S
D		Q	
		4/	U.
J		+	IF-de las
H	ľ	R	U.
F G	•		
			V.III
	- ma	Po.	1
		m	-
DIM	MIN 1	MAX	-
A		6.8	-
В	6.6		-
C D	15.23	15.25	-
	10.15 0.76	10.17	-
F	1.26	1.78	1
	1.20	1,20	4
	14	1.6	
H	1.4	0.78 1.28 1.6	-
H	1.4	1.35	
J K	1.4 1.33 0.4	1.35 0.6	
J K	1.4 1.33 0.4 4.6	1.35 0.6 4.8	
H J K L	1.4 1.33 0.4 4.6	1.35 0.6 4.8 8.71	
H J K L	1.4 1.33 0.4 4.6 8.69 5.28	1.35 0.6 4.8 8.71 5.30	
H J K L Q R	1.4 1.33 0.4 4.6 8.69 5.28 1.26	1.35 0.6 4.8 8.71 5.30	
H J K L	1.4 1.33 0.4 4.6 8.69 5.28	1.35 0.6 4.8 8.71 5.30	- a

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 1mA	600			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =±30V; I _D =0.25mA	2		4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =8A		200	220	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±25V;V _{DS} = 0V			±0.1	μА
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 600V; V _{GS} = 0V; T _J =25°C T _J =125°C			1 100	μА
V _{SDF}	Diode forward voltage	I _{SD} =16A, V _{GS} = 0 V			1.6	V

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